

Akira Uedono

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375
papers

5,869
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35
h-index

57
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422
ext. papers

6,437
ext. citations

2.4
avg, IF

5.38
L-index

#	Paper	IF	Citations
375	Origin of defect-insensitive emission probability in In-containing (Al,In,Ga)N alloy semiconductors. <i>Nature Materials</i> , 2006 , 5, 810-6	27	548
374	Correlation between the photoluminescence lifetime and defect density in bulk and epitaxial ZnO. <i>Applied Physics Letters</i> , 2003 , 82, 532-534	3.4	215
373	Limiting factors of room-temperature nonradiative photoluminescence lifetime in polar and nonpolar GaN studied by time-resolved photoluminescence and slow positron annihilation techniques. <i>Applied Physics Letters</i> , 2005 , 86, 021914	3.4	116
372	Defects in ZnO thin films grown on ScAlMgO ₄ substrates probed by a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2003 , 93, 2481-2485	2.5	98
371	Improvements in quantum efficiency of excitonic emissions in ZnO epilayers by the elimination of point defects. <i>Journal of Applied Physics</i> , 2006 , 99, 093505	2.5	96
370	Radiative and nonradiative processes in strain-free Al _x Ga _{1-x} N films studied by time-resolved photoluminescence and positron annihilation techniques. <i>Journal of Applied Physics</i> , 2004 , 95, 2495-2504	2.5	82
369	Study of defects in GaN grown by the two-flow metalorganic chemical vapor deposition technique using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2001 , 90, 181-186	2.5	80
368	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al _{0.6} Ga _{0.4} N films grown on AlN templates by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2013 , 113, 213506	2.5	73
367	The origins and properties of intrinsic nonradiative recombination centers in wide bandgap GaN and AlGa _N . <i>Journal of Applied Physics</i> , 2018 , 123, 161413	2.5	70
366	Generation of thermal muonium in vacuum. <i>Physical Review Letters</i> , 1986 , 56, 1463-1466	7.4	64
365	Exciton-polariton spectra and limiting factors for the room-temperature photoluminescence efficiency in ZnO. <i>Semiconductor Science and Technology</i> , 2005 , 20, S67-S77	1.8	61
364	Study of oxygen vacancies in SrTiO ₃ by positron annihilation. <i>Journal of Applied Physics</i> , 2002 , 92, 2697-2702	2.7	61
363	Relation between Al vacancies and deep emission bands in AlN epitaxial films grown by NH ₃ -source molecular beam epitaxy. <i>Applied Physics Letters</i> , 2007 , 90, 241914	3.4	60
362	Time-resolved photoluminescence, positron annihilation, and Al _{0.23} Ga _{0.77} N/GaN heterostructure growth studies on low defect density polar and nonpolar freestanding GaN substrates grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2012 , 111, 103518	2.5	56
361	Vacancy-oxygen complexes and their optical properties in AlN epitaxial films studied by positron annihilation. <i>Journal of Applied Physics</i> , 2009 , 105, 054501	2.5	54
360	Vacancy-type defects and their annealing behaviors in Mg-implanted GaN studied by a monoenergetic positron beam. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 2794-2801	1.3	52
359	Radiative and nonradiative excitonic transitions in nonpolar (112 0) and polar (0001) and (0001) ZnO epilayers. <i>Applied Physics Letters</i> , 2004 , 84, 1079-1081	3.4	50

358	Impact of growth polar direction on the optical properties of GaN grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2001 , 78, 28-30	3.4	50
357	Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. <i>Applied Physics Express</i> , 2017 , 10, 061002	2.4	49
356	The dependence of oxygen vacancy distributions in BiFeO ₃ films on oxygen pressure and substrate. <i>Applied Physics Letters</i> , 2009 , 95, 012904	3.4	48
355	Brightness enhancement method for a high-intensity positron beam produced by an electron accelerator. <i>Journal of Applied Physics</i> , 2008 , 103, 094916	2.5	48
354	A Study of Vacancy-Type Defects in B+-Implanted SiO ₂ /Si by a Slow Positron Beam. <i>Japanese Journal of Applied Physics</i> , 1989 , 28, 1293-1297	1.4	48
353	Native cation vacancies in Si-doped AlGa _{1-x} N studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2012 , 111, 013512	2.5	45
352	Recent advances and challenges for successful p-type control of InN films with Mg acceptor doping by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1011-1023	1.6	45
351	A study of agglomeration and release processes of helium implanted in nickel by a variable energy positron beam. <i>Journal of Nuclear Materials</i> , 1985 , 133-134, 463-467	3.3	45
350	Free and bound exciton fine structures in AlN epilayers grown by low-pressure metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2009 , 105, 023529	2.5	44
349	Transition and relaxation processes of polyethylene, polypropylene, and polystyrene studied by positron annihilation. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1997 , 35, 1601-1609	2.6	43
348	Effect of La doping on the lattice defects and photoluminescence properties of CuO. <i>Journal of Alloys and Compounds</i> , 2017 , 709, 496-504	5.7	42
347	Investigation of defect related photoluminescence property of multicolour emitting Gd ₂ O ₃ :Dy ³⁺ phosphor. <i>RSC Advances</i> , 2014 , 4, 34257	3.7	41
346	Carrier Trapping by Vacancy-Type Defects in Mg-Implanted GaN Studied Using Monoenergetic Positron Beams. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700521	1.3	39
345	Point defects in group-III nitride semiconductors studied by positron annihilation. <i>Journal of Crystal Growth</i> , 2009 , 311, 3075-3079	1.6	39
344	Rapid three-dimensional imaging of defect distributions using a high-intensity positron microbeam. <i>Applied Physics Letters</i> , 2009 , 94, 194104	3.4	38
343	Improvement of crystal quality of GaInNAs films grown by atomic hydrogen-assisted RF-MBE. <i>Journal of Crystal Growth</i> , 2005 , 278, 553-557	1.6	38
342	Synthesis, defect characterization and photocatalytic degradation efficiency of Tb doped CuO nanoparticles. <i>Advanced Powder Technology</i> , 2017 , 28, 3026-3038	4.6	37
341	Low temperature buffer growth for modulation doped SiGe/Ge/SiGe heterostructures with high hole mobility. <i>Thin Solid Films</i> , 2000 , 369, 320-323	2.2	35

340	Large electron capture-cross-section of the major nonradiative recombination centers in Mg-doped GaN epilayers grown on a GaN substrate. <i>Applied Physics Letters</i> , 2018 , 112, 211901	3.4	35
339	Recent Progress in Gas Barrier Thin Film Coatings on PET Bottles in Food and Beverage Applications. <i>Coatings</i> , 2015 , 5, 987-1001	2.9	34
338	Annealing properties of vacancy-type defects in ion-implanted GaN studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2007 , 102, 084505	2.5	34
337	Defect Production in Phosphorus Ion-Implanted SiO ₂ (43 nm)/Si Studied by a Variable-Energy Positron Beam. <i>Japanese Journal of Applied Physics</i> , 1991 , 30, 201-206	1.4	34
336	Positronium formation in SiO ₂ films grown on Si substrates studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 1994 , 75, 3822-3828	2.5	33
335	Annealing Properties of Defects in B ⁺ - and F ⁺ -Implanted Si Studied Using Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 2571-2580	1.4	32
334	Metal ion binding properties of novel wool powders. <i>Journal of Applied Polymer Science</i> , 2010 , 115, 1642-1650	2.1	31
333	Nanoporous structure of methyl-silsesquioxane films using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2001 , 90, 2498-2503	2.5	31
332	Vacancy-type defects in BaTiO ₃ /SrTiO ₃ structures probed by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2002 , 91, 5307-5312	2.5	31
331	AlN metal-semiconductor field-effect transistors using Si-ion implantation. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FR11	1.4	30
330	Defect-Resistant Radiative Performance of m-Plane Immiscible Al In N Epitaxial Nanostructures for Deep-Ultraviolet and Visible Polarized Light Emitters. <i>Advanced Materials</i> , 2017 , 29, 1603644	2.4	30
329	Reduced defect densities in the ZnO epilayer grown on Si substrates by laser-assisted molecular-beam epitaxy using a ZnS epitaxial buffer layer. <i>Applied Physics Letters</i> , 2004 , 85, 5586-5588	3.4	30
328	Positron annihilation in electron irradiated Cz-Si. <i>Hyperfine Interactions</i> , 1993 , 79, 615-619	0.8	30
327	Vacancy-type defects in Si ⁺ -implanted GaAs and its effects on electrical activation by rapid thermal annealing. <i>Journal of Applied Physics</i> , 1990 , 67, 6153-6158	2.5	30
326	Effect of Free-Volume Holes on Dynamic Mechanical Properties of Epoxy Resins for Carbon-Fiber-Reinforced Polymers. <i>Macromolecules</i> , 2017 , 50, 3933-3942	5.5	29
325	Leaching properties of chromate-containing epoxy films using radiotracers, PALS and SEM. <i>Progress in Organic Coatings</i> , 2014 , 77, 257-267	4.8	29
324	Defect characterization in Mg-doped GaN studied using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2012 , 111, 014508	2.5	28
323	Characterization of Grown-in Dislocations in Benzophenone Single Crystals by X-Ray Topography. <i>Japanese Journal of Applied Physics</i> , 1992 , 31, 2202-2205	1.4	28

3 ²²	Formation of low resistance ohmic contacts in GaN-based high electron mobility transistors with BCl ₃ surface plasma treatment. <i>Applied Physics Letters</i> , 2013 , 103, 083508	3.4	27
3 ²¹	First-principles calculation of positron states and annihilation parameters for group-III nitrides. <i>Journal of Physics: Conference Series</i> , 2014 , 505, 012010	0.3	26
3 ²⁰	Major impacts of point defects and impurities on the carrier recombination dynamics in AlN. <i>Applied Physics Letters</i> , 2010 , 97, 201904	3.4	26
3 ¹⁹	Epitaxial growth of BaTiO ₃ /SrTiO ₃ structures on SrTiO ₃ substrate with automatic feeding of oxygen from the substrate. <i>Journal of Applied Physics</i> , 2002 , 92, 4625-4630	2.5	26
3 ¹⁸	Room-temperature photoluminescence lifetime for the near-band-edge emission of (000 1 $\bar{1}$) p-type GaN fabricated by sequential ion-implantation of Mg and H. <i>Applied Physics Letters</i> , 2018 , 113, 191901	3.4	26
3 ¹⁷	Behavior of oxygen vacancies in BiFeO ₃ /SrRuO ₃ /SrTiO ₃ (100) and DyScO ₃ (100) heterostructures. <i>Applied Physics Letters</i> , 2009 , 94, 132905	3.4	25
3 ¹⁶	Defects Introduced by MeV-Energy Ion Implantation into Si Probed by a Monoenergetic Positron Beam. <i>Japanese Journal of Applied Physics</i> , 1991 , 30, 1597-1603	1.4	25
3 ¹⁵	Metal/oxide/semiconductor interface investigated by monoenergetic positrons. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1988 , 133, 82-84	2.3	25
3 ¹⁴	Variable-energy positron-beam studies of SiO ₂ /Si irradiated by ionizing radiation. <i>Applied Physics Letters</i> , 1988 , 53, 473-475	3.4	25
3 ¹³	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi ₂ films by Raman spectroscopy. <i>Applied Physics Express</i> , 2019 , 12, 055506	2.4	24
3 ¹²	Identification of extremely radiative nature of AlN by time-resolved photoluminescence. <i>Applied Physics Letters</i> , 2010 , 96, 061906	3.4	24
3 ¹¹	Vacancy-type defects in Er-doped GaN studied by a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2008 , 103, 104505	2.5	24
3 ¹⁰	Origin of localized excitons in In-containing three-dimensional bulk (Al,In,Ga)N alloy films probed by time-resolved photoluminescence and monoenergetic positron annihilation techniques. <i>Philosophical Magazine</i> , 2007 , 87, 2019-2039	1.6	24
3 ⁰⁹	Positron annihilation in SiO ₂ /Si studied by a pulsed slow positron beam. <i>Applied Surface Science</i> , 2002 , 194, 89-96	6.7	24
3 ⁰⁸	Vacancy-Type Defects in As ⁺ -Implanted SiO ₂ (43 nm)/Si Probed with Slow Positrons. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, 1867-1872	1.4	24
3 ⁰⁷	Vacancy-type defects in Mg-doped InN probed by means of positron annihilation. <i>Journal of Applied Physics</i> , 2009 , 105, 054507	2.5	23
3 ⁰⁶	Collateral evidence for an excellent radiative performance of Al _x Ga _{1-x} N alloy films of high AlN mole fractions. <i>Applied Physics Letters</i> , 2011 , 99, 051902	3.4	23
3 ⁰⁵	Effects of Recoil-Implanted Oxygen on Depth Profiles of Defects and Annealing Processes in P ⁺ -Implanted Si Studied Using Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 2000-2007	1.4	23

304	Impact of Al in Cu alloy interconnects on electro and stress migration reliabilities. <i>Microelectronic Engineering</i> , 2008 , 85, 2137-2141	2.5	23
303	Characterization of vacancy-type defects and phosphorus donors introduced in 6H-SiC by ion implantation. <i>Applied Physics A: Materials Science and Processing</i> , 1998 , 67, 407-412	2.6	22
302	Hydrogen-terminated defects in ion-implanted silicon probed by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2003 , 93, 3228-3233	2.5	22
301	Investigation of Positron Moderator Materials for Electron-Linac-Based Slow Positron Beamlines. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 4636-4643	1.4	22
300	Depth profile of vacancy-type defects in B ⁺ -implanted Si with a SiO ₂ overlayer by a variable-energy positron beam. <i>Applied Physics Letters</i> , 1988 , 53, 25-27	3.4	22
299	Excitonic emission dynamics in homoepitaxial AlN films studied using polarized and spatio-time-resolved cathodoluminescence measurements. <i>Applied Physics Letters</i> , 2013 , 103, 142103	3.4	21
298	In-situ characterization of free-volume holes in polymer thin films under controlled humidity conditions with an atmospheric positron probe microanalyzer. <i>Applied Physics Letters</i> , 2012 , 101, 014102 ^{3,4}		21
297	Characterization of Separation-by-Implanted-Oxygen Wafers with Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 3682-3686	1.4	21
296	Characterization of Diamond Films Synthesized on Si from a Gas Phase in Microwave Plasma by Slow Positrons. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, 555-559	1.4	21
295	Enhanced photo/electroluminescence properties of Eu-doped GaN through optimization of the growth temperature and Eu related defect environment. <i>APL Materials</i> , 2016 , 4, 056103	5.7	21
294	Positron Annihilation Spectroscopy on Nitride-Based Semiconductors. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JJ02	1.4	20
293	Thermal stability of semi-insulating property of Fe-doped GaN bulk films studied by photoluminescence and monoenergetic positron annihilation techniques. <i>Journal of Applied Physics</i> , 2009 , 105, 083542	2.5	20
292	Vacancy-type defects in In _x Ga _{1-x} N alloys probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2012 , 112, 014507	2.5	20
291	Defects introduced into electroplated Cu films during room-temperature recrystallization probed by a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2005 , 98, 043504	2.5	20
290	Characterization of low temperature grown Si layer for SiGe pseudo-substrates by positron annihilation spectroscopy. <i>Journal of Crystal Growth</i> , 2001 , 227-228, 761-765	1.6	20
289	Positron Annihilation in Proton Irradiated Czochralski-Grown Si. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 1-5	1.4	20
288	Low-resistivity-m-plane freestanding GaN substrate with very low point-defect concentrations grown by hydride vapor phase epitaxy on a GaN seed crystal synthesized by the ammonothermal method. <i>Applied Physics Express</i> , 2015 , 8, 095501	2.4	19
287	Open spaces in the subsurface region of polyethylene probed by monoenergetic positron beams. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1998 , 36, 2597-2605	2.6	19

286	Vacancy-type defects in electroplated Cu films probed by using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2004 , 95, 913-918	2.5	19
285	Study of various types of diamonds by measurements of double crystal x-ray diffraction and positron annihilation. <i>Journal of Applied Physics</i> , 1995 , 78, 1510-1513	2.5	19
284	Study of relaxation processes in polyethylene and polystyrene by positron annihilation. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1996 , 34, 2145-2151	2.6	19
283	Influence of Si wafer thinning processes on (sub)surface defects. <i>Applied Surface Science</i> , 2017 , 404, 82-87	1.8	18
282	Optically active vacancies in GaN grown on Si substrates probed using a monoenergetic positron beam. <i>Applied Physics Letters</i> , 2014 , 104, 082110	3.4	18
281	Impact of back-grinding-induced damage on Si wafer thinning for three-dimensional integration. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05GE04	1.4	18
280	A positron annihilation lifetime measurement system with an intense positron microbeam. <i>Radiation Physics and Chemistry</i> , 2009 , 78, 1096-1098	2.5	18
279	Characterization of HfSiON gate dielectrics using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2006 , 99, 054507	2.5	18
278	Direct comparison of photoluminescence lifetime and defect densities in ZnO epilayers studied by time-resolved photoluminescence and slow positron annihilation techniques. <i>Physica Status Solidi A</i> , 2004 , 201, 2841-2845		18
277	Annealing properties of defects during Si-on-insulator fabrication by low-dose oxygen implantation studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2000 , 87, 1659-1665	2.5	18
276	Free volumes in polystyrene probed by positron annihilation. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1996 , 34, 1189-1195	2.6	18
275	Defects in electron irradiated vitreous SiO ₂ probed by positron annihilation. <i>Journal of Physics Condensed Matter</i> , 1994 , 6, 8669-8677	1.8	18
274	Vacancies and electron trapping centers in acidic ammonothermal GaN probed by a monoenergetic positron beam. <i>Journal of Crystal Growth</i> , 2016 , 448, 117-121	1.6	17
273	Improvement of hydrogen absorption rate of Pd by ion irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003 , 206, 224-227	1.2	17
272	Defects in Eu- and Tb-doped GaN probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2003 , 93, 5181-5184	2.5	17
271	Free volumes in liquid-crystalline main-chain polymer probed by positron annihilation. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1995 , 33, 891-897	2.6	17
270	SiO ₂ films deposited on Si substrates studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 1994 , 75, 216-222	2.5	17
269	Impact of Cu/III ratio on the near-surface defects in polycrystalline CuGaSe ₂ thin films. <i>Applied Physics Letters</i> , 2011 , 98, 112105	3.4	16

268	Vacancy-Boron Complexes in Plasma Immersion Ion-Implanted Si Probed by a Monoenergetic Positron Beam. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 051301	1.4	16
267	Impact of Point Defects on the Luminescence Properties of (Al,Ga)N. <i>Materials Science Forum</i> , 2008 , 590, 233-248	0.4	16
266	Annealing properties of open volumes in HfSiOx and HfAlOx gate dielectrics studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2005 , 98, 023506	2.5	16
265	Free Volume in Polycarbonate Studied by Positron Annihilation: Effects of Free Radicals and Trapped Electrons on Positronium Formation. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 5036-5040	1.4	16
264	Positron Annihilation in Vitreous Silica Glasses. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 2687-2691	1.4	16
263	Characterization of Diamond Films by Means of a Pulsed Positron Beam. <i>Japanese Journal of Applied Physics</i> , 1992 , 31, 2237-2240	1.4	16
262	Annealing Behavior of Vacancy-Type Defects in Mg- and H-Implanted GaN Studied Using Monoenergetic Positron Beams. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1900104	1.3	15
261	Surface sealing using self-assembled monolayers and its effect on metal diffusion in porous low- k dielectrics studied using monoenergetic positron beams. <i>Applied Surface Science</i> , 2016 , 368, 272-276	6.7	15
260	Using X-ray tomography, PALS and Raman spectroscopy for characterization of inhibitors in epoxy coatings. <i>Progress in Organic Coatings</i> , 2012 , 74, 726-733	4.8	15
259	Annealing Properties of Defects in Ion-Implanted 3C-SiC Studied Using Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 6650-6660	1.4	15
258	Thermal variation of free-volumes size distribution in polypropylenes. Probed by positron annihilation lifetime technique. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , 1995 , 33, 1183-1190	2.6	15
257	Vacancy-Type Defects in Ion-Implanted Diamonds Probed by Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1995 , 34, 1772-1777	1.4	15
256	Positron Study of Vacancy-Type Defects Induced by Heavy Doping into MBE-Grown GaAs. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, L346-L348	1.4	15
255	Defects Induced by Wafer Processing and Thermal Treatment in InP Probed with Monoenergetic Positrons. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, 909-912	1.4	15
254	Room temperature photoluminescence lifetime for the near-band-edge emission of epitaxial and ion-implanted GaN on GaN structures. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC0802	1.4	14
253	Impact of Se flux on the defect formation in polycrystalline Cu(In,Ga)Se ₂ thin films grown by three stage evaporation process. <i>Journal of Applied Physics</i> , 2013 , 113, 064907	2.5	14
252	Slow Positron Beam Apparatus for Surface and Subsurface Analysis of Samples in Air. <i>Applied Physics Express</i> , 2011 , 4, 066701	2.4	14
251	Defects in Ion-Implanted 3CβSiC Probed by a Monoenergetic Positron Beam. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 5986-5990	1.4	14

250	Vacancy-type defects in Si-doped InN grown by plasma-assisted molecular-beam epitaxy probed using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2005 , 97, 043514	2.5	14
249	Crystallization of an amorphous layer in P+-implanted 6H-SiC studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2000 , 87, 4119-4125	2.5	14
248	Positron annihilation in silicon in thermal equilibrium at high temperature. <i>Journal of Physics Condensed Matter</i> , 2000 , 12, 719-728	1.8	14
247	Depth profiles on ion implantation induced vacancy-type defects in GaAs and Si observed by slow positron. <i>Applied Physics Letters</i> , 1988 , 53, 1302-1304	3.4	14
246	Probing the effect of point defects on the leakage blocking capability of Al _{0.1} Ga _{0.9} N/Si structures using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2016 , 120, 215702	2.5	14
245	Valence band edge tail states and band gap defect levels of GaN bulk and In _x Ga _{1-x} N films detected by hard X-ray photoemission and photothermal deflection spectroscopy. <i>Applied Physics Express</i> , 2018 , 11, 021002	2.4	13
244	Vacancy-type defects in Al ₂ O ₃ /GaN structure probed by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2018 , 123, 155302	2.5	13
243	Characterization of residual defects in cubic silicon carbide subjected to hot-implantation and subsequent annealing. <i>Journal of Applied Physics</i> , 1997 , 82, 5339-5347	2.5	13
242	Effect of growth temperature on the properties of Ga(In)NAs thin films by atomic hydrogen-assisted RF-MBE. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 579-582	1.6	13
241	Homoepitaxial Growth of SrTiO ₃ in an Ultrahigh Vacuum with Automatic Feeding of Oxygen from the Substrate at Temperatures as Low as 370°C. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L269-L271 ^{1.4}	1.4	13
240	Molecular motion and relaxation below glass transition temperature in poly (methyl methacrylate) studied by positron annihilation. <i>Radiation Physics and Chemistry</i> , 2015 , 108, 81-86	2.5	12
239	Positron annihilation studies of defects in 3CSiC hot-implanted with nitrogen and aluminum ions. <i>Applied Physics A: Materials Science and Processing</i> , 1997 , 65, 315-323	2.6	12
238	Local Bonding Structure of High-Stress Silicon Nitride Film Modified by UV Curing for Strained Silicon Technology beyond 45 nm Node SoC Devices. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 1984-1988 ^{1.4}	1.4	12
237	Defects in CeO ₂ /SrTiO ₃ fabricated by automatic feeding epitaxy probed using positron annihilation. <i>Journal of Applied Physics</i> , 2003 , 94, 5193	2.5	12
236	Annihilation of positronium in alpha -SiO ₂ investigated by combined angular correlation and lifetime measurements. <i>Physical Review B</i> , 1996 , 54, 15051-15055	3.3	12
235	Release processes of He implanted in Cu and Ni studied by a monoenergetic positron beam. <i>Journal of Nuclear Materials</i> , 1991 , 184, 191-196	3.3	12
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